

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**INFORMATION DISCLOSURE STATEMENT**

APPLICANT(S): Osamu Goto, et al. DOCKET NO.: 09792909-5625  
SERIAL NO.: Unknown GROUP ART UNIT: Unknown  
DATE FILED: June 25, 2003 EXAMINER: Unknown  
INVENTION: "SEMICONDUCTOR LIGHT EMITTING DEVICE, ITS  
MANUFACTURING METHOD, SEMICONDUCTOR DEVICE,  
AND ITS MANUFACTURING METHOD"

Mail Stop: PCT  
Commissioner for Patents  
P.O. Box 1450  
Arlington, VA 22313-1450

SIR:

In accordance with the provisions of 37 C.F.R. § 1.56, Applicants request that citation and examination of the references identified on the attached PTO-1449 form, copies of which are enclosed herewith in accordance with 37 C.F.R. § 1.98, be made during the course of examination of the above-referenced application for United States Letters Patent.

**I. SUBMITTED US PATENT REFERENCES**

<u>Number</u>	<u>Country</u>	<u>Date of Publication</u>
6,060,335	U.S.	May 9, 2000

**II. SUBMITTED FOREIGN PATENT REFERENCES**

<u>Number</u>	<u>Country</u>	<u>Date of Publication</u>
JP11-54794	Japan	February 26, 1999
JP09-266326	Japan	October 7, 1997
JP11-243251	Japan	September 7, 1999
EP 0 803 916	Europe	October 3, 1999

### III. OTHER ITEMS OF INFORMATION

AT Shuji Nakamura, et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes", Applied Physics Letters, 1996, Vol. 68, No. 23, pp. 3269-3271.

#### IV. EXPLANATION OF RELEVANCE

The above-identified references were cited in the Japanese Patent Office Search Report of March 26, 2002, in counterpart PCT/JP01/11536. A copy of the Search Report is submitted herewith.

Submitted by,

  
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37 CFR 1.501  
 INFORMATION DISCLOSURE STATEMENT  
 IN A PATENT  
 (use several sheets if necessary)

Docket No.  
 09792909-5625

Serial No.

Applicants:  
 Osamu Goto, et al.

Filing Date  
 June 25, 2003

Group Art Unit

**U.S. PATENT DOCUMENTS**

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
AA		6,060,335	5-9-00	Rennie			
AB							
AC							
AD							
AE							
AF							
AG							

**FOREIGN PATENT DOCUMENTS**

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
AH		JP11-54794	2-26-99	Japan			Abstract	
AI		JP09-266326	10-7-97	Japan			Abstract	
AJ		JP11-243251	9-7-99	Japan			Abstract	
AK		EP 0 803 916	10-29-99	Europe				
AL								
AM								
AN								
AO								
AP								
AQ								
AR								
AS								

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

AT	Shuji Nakamura, et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes", Applied Physics Letters, 1996, Vol. 68, No. 23, pp. 3269-3271
AU	
AV	
AW	
AX	
AY	
AZ	

Examiner Date Considered

**\*EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.